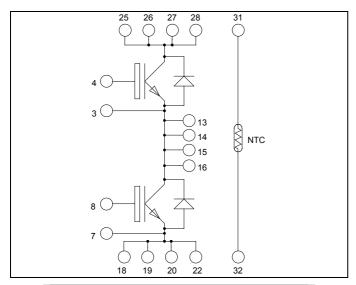
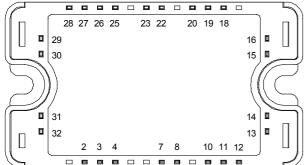


## Phase leg NPT IGBT Power Module

$$V_{CES} = 1200V$$
  
 $I_{C} = 150A$  @  $Tc = 80$ °C





Pins 25/26/27/28 must be shorted together Pins 13/14/15/16 must be shorted together Pins 18/19/20/22 must be shorted together

### Application

• Welding converters

#### **Features**

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive T<sub>C</sub> of V<sub>CEsat</sub>
- RoHS compliant

#### **Absolute maximum ratings**

IIDSOIGE	·			
Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
ī	Continuous Collector Current	$T_C = 25^{\circ}C$	210	
$I_{C}$	Continuous Conector Current	$T_C = 80$ °C	150	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	300	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	961	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm J} = 150^{\circ}{\rm C}$	300A @ 1150V	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		3.2	3.7	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_{\rm C} = 150 {\rm A}$ $T_{\rm j} =$	$T_j = 125$ °C		3.9		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 6mA$		4.5	5.5	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

**Dynamic Characteristics** 

Symbol	Characteristic	Test Condition	Test Conditions		Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			9.3		
Coes	Output Capacitance	$V_{CE} = 25V$	$V_{CE} = 25V$ $f = 1MHz$		1.4		nF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			0.7		
$Q_{G}$	Gate charge	$V_{GE} = \pm 15V ; V$ $I_{C} = 150A$	$V_{GE} = \pm 15V ; V_{CE} = 600V$ $I_{C} = 150A$		1.6		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Swite	ching (25°C)		120		ns
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			50		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600V$ $I_{\text{C}} = 150A$			310		
$T_{\rm f}$	Fall Time	$R_G = 5.6\Omega$	_		20		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_{C} = 150A$ $R_{G} = 5.6\Omega$		130		ns
$T_{\rm r}$	Rise Time				60		
$T_{d(off)}$	Turn-off Delay Time				360	)	
$T_{\mathrm{f}}$	Fall Time	$R_G = 5.6\Omega$			30		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		18		Т
$E_{\text{off}}$	Turn-off Switching Energy	$I_C = 150A$ $R_G = 5.6\Omega$	$T_j = 125$ °C		8		mJ
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V$ ; $V_B$ $t_p \le 10 \mu s$ ; $T_i =$			900		A

**Reverse diode ratings and characteristics** 

Symbol	Characteristic		Test Conditions		Тур	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
т	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_j = 25^{\circ}C$			100	۸
$I_{RM}$		V <sub>R</sub> −1200 V	$T_j = 125$ °C			500	μΑ
$I_F$	DC Forward Current		$Tc = 80^{\circ}C$		100		Α
	Diode Forward Voltage	$I_{\rm F} = 100 A$			2.4	3	
$V_{\rm F}$		$I_F = 200A$			2.7		V
		$I_F = 100A   T_j$	$T_j = 125$ °C		1.8		
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25$ °C		385		ns
·rr		$I_F = 100A$ $V_R = 800V$	$T_{\rm j} = 125^{\circ}{\rm C}$		480		115
Q <sub>rr</sub>	Reverse Recovery Charge	$di/dt = 200A/\mu s$	$T_j = 25$ °C		1055		пC
			$T_{\rm j} = 125^{\circ}{\rm C}$		5240		пС



 $Temperature\ sensor\ NTC\ (\text{see application note APT0406 on www.microsemi.com for more information}).$ 

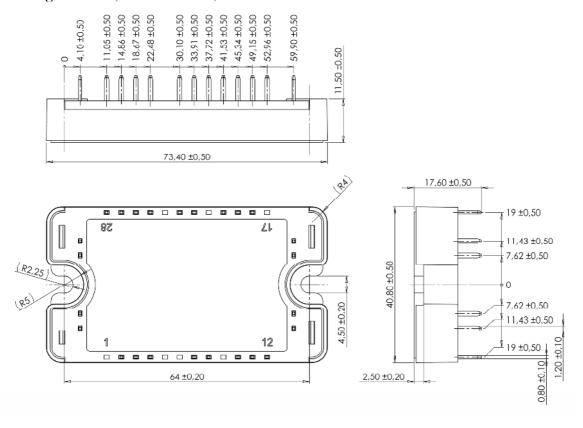
Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		T <sub>C</sub> =100°C		4		%

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$
 
$$R_{T}: \text{ Thermistor value at T}$$

## Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case thermal resistance		IGBT			0.13	°C/W
TthJC			Diode			0.55	C/ W
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range			-40		150	
$T_{STG}$	Storage Temperature Range		-40		125	°C	
$T_{C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

### SP3 Package outline (dimensions in mm)

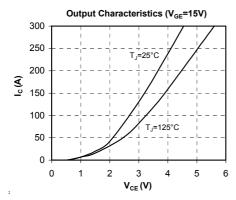


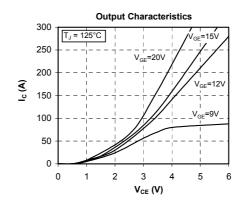
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

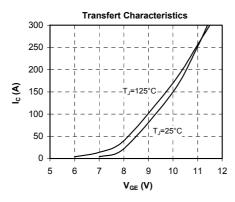
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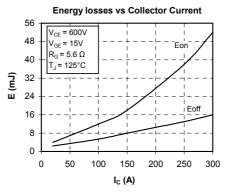


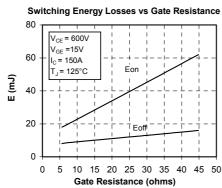
### **Typical Performance Curve**

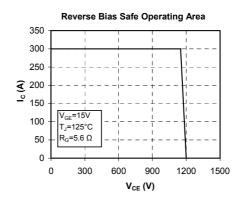


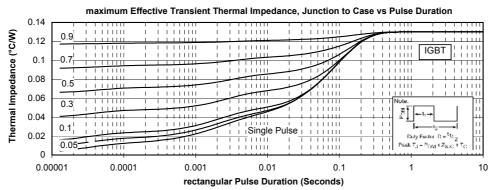




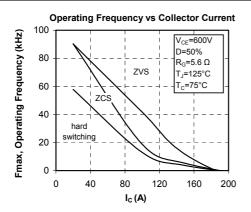


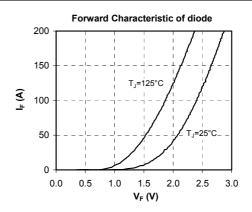


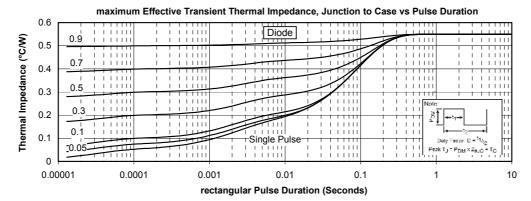












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